



# TF1503U

## Half-Bridge Gate Driver

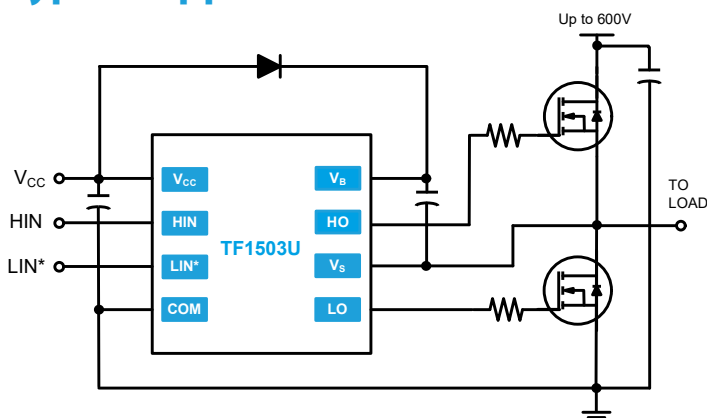
### Features

- Floating high-side driver in bootstrap operation to 600V
- Drives two N-channel MOSFETs or IGBTs in a half bridge configuration
- Designed for enhanced performance in noisy motor applications
- 300mA source/550mA sink output current capability
- Outputs tolerant to negative transients
- Internal dead time of 420ns to protect MOSFETs
- Wide low side gate driver supply voltage: 10V to 20V
- Logic input (HIN and LIN\*) 3.3V capability
- Schmitt triggered logic inputs
- Undervoltage lockout for  $V_{CC}$  (logic and low side supply)
- Extended temperature range:  $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$

### Applications

- Motor Controls
- DC-DC Converters
- AC-DC Inverters
- Motor Drives

### Typical Application



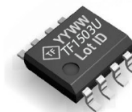
### Description

The TF1503U is a high voltage, high speed gate driver capable of driving N-channel MOSFETs and IGBTs in a half bridge configuration. TF Semiconductor's high voltage process enables the TF2103U high side to switch to 250V in a bootstrap operation.

The TF1503U logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with controlling devices. The driver outputs feature high pulse current buffers designed for minimum driver cross conduction. TF1503U has a fixed internal deadtime of 420ns (typical).

The TF1503U is offered in a SOIC-8(N) package and operates over an extended  $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$  temperature range.

SOIC-8(N)



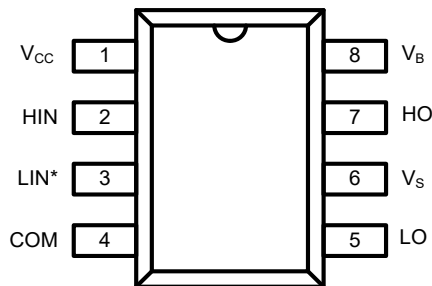
### Ordering Information

Year Year Week Week

PART NUMBER	PACKAGE	PACK / Qty	MARK
TF1503U-TAU	SOIC-8(N)	Tube / 100	YYWW TF1503U
TF1503U-TAH	SOIC-8(N)	T&R / 2500	LotID



## Pin Diagrams



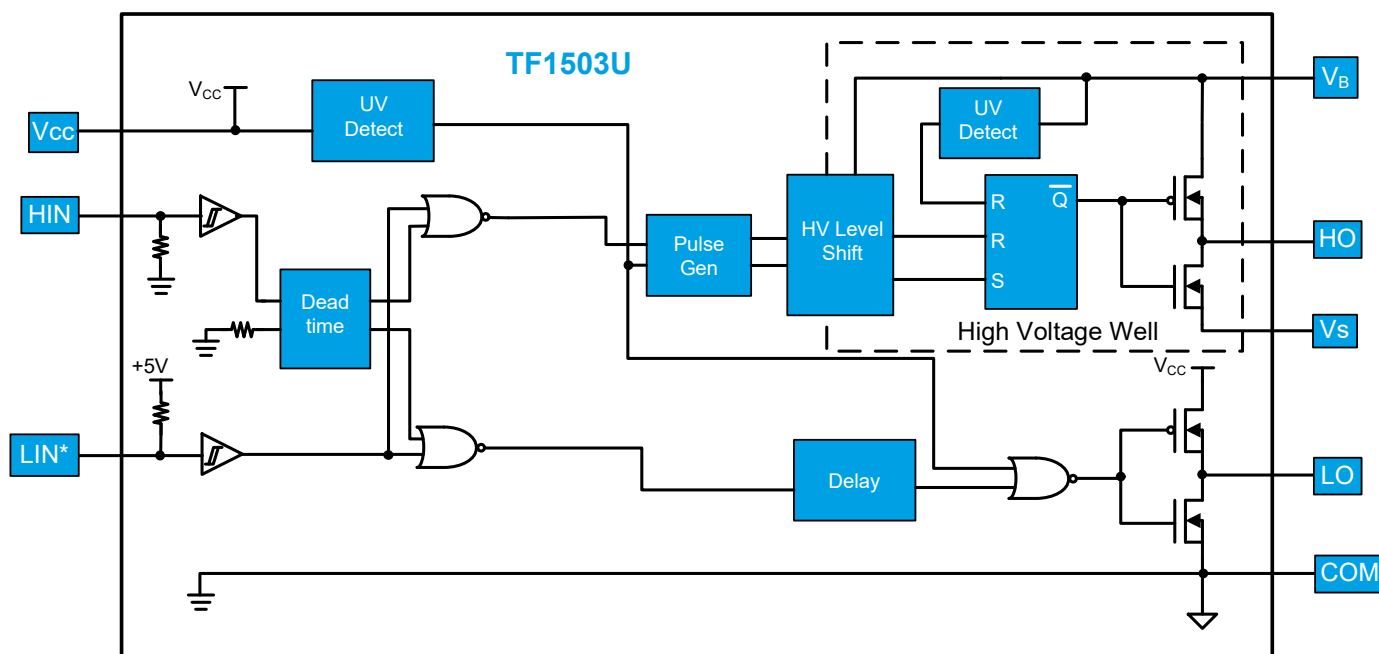
**Top View: SOIC-8**

**TF1503U**

## Pin Descriptions

PIN NAME	PIN NUMBER	PIN DESCRIPTION
V <sub>CC</sub>	1	Logic and low side supply
HIN	2	Logic input for high-side gate driver output in phase with HO
LIN*	3	Logic input for low-side gate driver output out of phase with LO
COM	4	Low-side and logic return
LO	5	Low-side gate drive output
V <sub>S</sub>	6	High-side floating supply return
HO	7	High-side gate drive output
V <sub>B</sub>	8	High-side floating supply

## Functional Block Diagram





## Half-Bridge Gate Driver

## Absolute Maximum Ratings (NOTE1)

$V_B$  - High side floating supply voltage.....-0.3V to +274V  
 $V_S$  - High side floating supply offset voltage... $V_B$ -24V to  $V_B$ +0.3V  
 $V_{HO}$  - High side floating output voltage..... $V_S$ -0.3V to  $V_B$ +0.3V  
 $dV_S/dt$  - Offset supply voltage transient.....50 V/ns

$V_{CC}$  - Low-side fixed supply voltage.....-0.3V to +24V  
 $V_{LO}$  - Low-side output voltage.....-0.3V to  $V_{CC}$ +0.3V  
 $V_{IN}$  - Logic input voltage (HIN and LIN\*).....-0.3V to  $V_{CC}$ +0.3V

**NOTE1** Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

$P_D$  - Package power dissipation at  $T_A \leq 25^\circ\text{C}$   
 SOIC-8.....0.625W

SOIC-8(N) Thermal Resistance (NOTE2)

$\theta_{JA}$ .....200  $^\circ\text{C}/\text{W}$

$T_J$  - Junction operating temperature.....+150  $^\circ\text{C}$

$T_L$  - Lead Temperature (soldering, 10 seconds).....+300  $^\circ\text{C}$

$T_{stg}$  - Storage temperature .....-55 to 150  $^\circ\text{C}$

**NOTE2** When mounted on a standard JEDEC 2-layer FR-4 board.

## Recommended Operating Conditions

Symbol	Parameter	MIN	MAX	Unit
$V_B$	High side floating supply absolute voltage	$V_S + 10$	$V_S + 20$	V
$V_S$	High side floating supply offset voltage	<b>NOTE3</b>	250	V
$V_{HO}$	High side floating output voltage	$V_S$	$V_B$	V
$V_{CC}$	Low side fixed supply voltage	10	20	V
$V_{LO}$	Low side output voltage	0	$V_{CC}$	V
$V_{IN}$	Logic input voltage (HIN and LIN*)	0	5	V
$T_A$	Ambient temperature	-40	125	$^\circ\text{C}$

**NOTE3** Logic operational for  $V_S$  of -5V to +600V.



## DC Electrical Characteristics (NOTE4)

$V_{BIAS} (V_{CC}, V_{BS}) = 15V, T_A = 25^\circ C$ , unless otherwise specified.

Symbol	Parameter	Conditions	MIN	TYP	MAX	Unit
$V_{IH}$	Logic "1" (HIN) & Logic "0" (LIN*) input voltage	$V_{CC} = 10V$ to $20V$ <b>NOTES</b>	2.5			V
$V_{IL}$	Logic "0" (HIN) & Logic "1" (LIN*) input voltage					
$V_{OH}$	High level output voltage, $V_{BIAS} - V_O$	$I_O = 2mA$		0.05	0.2	
$V_{OL}$	Low level output voltage, $V_O$	$I_O = 2mA$		0.02	0.1	
$I_{LK}$	Offset supply leakage current	$V_B = V_S = 250V$			50	$\mu A$
$I_{BSQ}$	Quiescent $V_{BS}$ supply current	$V_{IN} = 0V$ or $5V$		7	50	
$I_{CCQ}$	Quiescent $V_{CC}$ supply current	$V_{IN} = 0V$ or $5V$		350	500	
$I_{IN+}$	Logic "1" input bias current	$HIN = 5V, LIN^* = 0V$		3	10	
$I_{IN-}$	Logic "0" input bias current	$HIN = 0V, LIN^* = 5V$			5	
$V_{CCUV+}$	$V_{CC}$ supply under-voltage positive going threshold		7.0	8.4	9.8	V
$V_{CCUV-}$	$V_{CC}$ supply under-voltage negative going threshold		6.5	7.8	9.3	
$V_{BSUV+}$	$V_{BS}$ supply under-voltage positive going threshold		3.6	4.5	5.6	V
$V_{BSUV-}$	$V_{BS}$ supply under-voltage negative going threshold		3	3.7	4.6	V
$I_{O+}$	Output high short circuit pulsed current	$V_O = 0V, PW \leq 10 \mu s$	130	300		mA
$I_{O-}$	Output low short circuit pulsed current	$V_O = 15V, PW \leq 10 \mu s$	270	550		

**NOTE4** The  $V_{IH}$ ,  $V_{IL}$ , and  $I_{IN}$  parameters are applicable to the two logic input pins: HIN and LIN\*. The  $V_O$  and  $I_O$  parameters are applicable to the respective output pins: HO and LO.

**NOTES** For optimal operation, it is recommended that the input pulse (to IN and SD\*) should have an amplitude of 2.5V minimum with a pulse width of 1 $\mu s$  minimum.

**AC Electrical Characteristics**

$V_{BIAS} (V_{CC}, V_{BS}) = 15V$ ,  $C_L = 1000pF$ , and  $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise specified.

Symbol	Parameter	Conditions	MIN	TYP	MAX	Unit
$t_{on}$	Turn-on propagation delay	$V_S = 0V$		560	820	ns
$t_{off}$	Turn-off propagation delay	$V_S = 250V$		150	220	
$t_{DM}$	Delay matching, HS & LS turn-on/turn-off				70	
$t_r$	Turn-on rise time	$V_S = 0V$		80	170	
$t_f$	Turn-off fall time			35	90	
$t_{DT}$	Deadtime: $t_{DT LO-HO}$ & $t_{DT HO-LO}$		300	420	650	



# Timing Waveforms

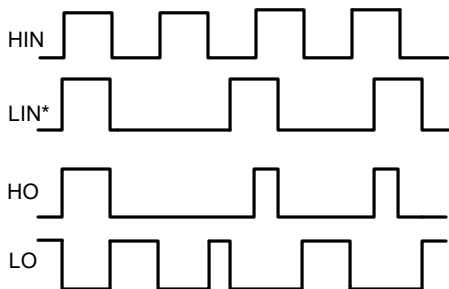


Figure 1. Input / Output Timing Diagram

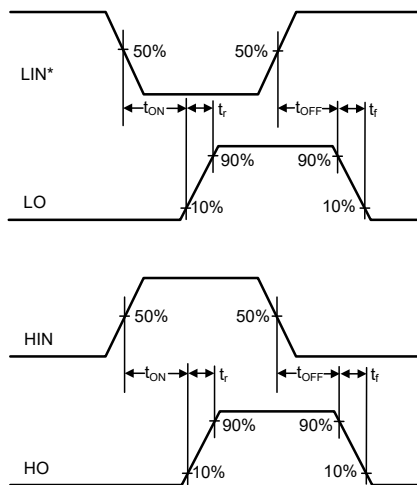


Figure 2. Switching Time Waveform Definitions

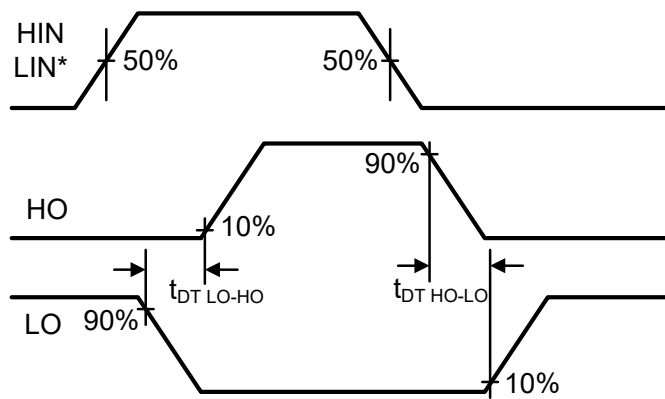


Figure 3. Deadtime Waveform Definitions





## Revision History

Rev.	Change	Owner	Date
1.0	First release, AI datasheet	Duke Walton	04/10/2020

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